

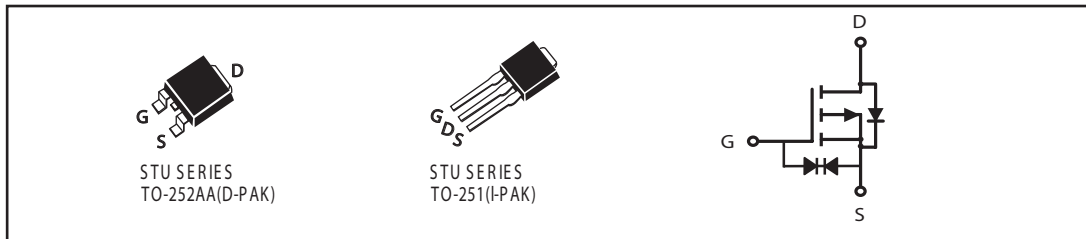


## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
-30V	-24A	28 @ V <sub>GS</sub> = -10V
		40 @ V <sub>GS</sub> = -4.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous @ T <sub>C</sub> =25°C -Pulsed <sup>a</sup>	I <sub>D</sub>	-24	A
	I <sub>DM</sub>	-96	A
Drain-Source Diode Forward Current	I <sub>S</sub>	-20	A
Maximum Power Dissipation @ T <sub>C</sub> =25°C	P <sub>D</sub>	50	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 175	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	50	°C/W

# STU/D303S

ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit	
<b>OFF CHARACTERISTICS</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250uA	-30			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V			-1	uA	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±10	uA	
<b>ON CHARACTERISTICS<sup>a</sup></b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1	-1.8	-3	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -12A		23	28	m ohm	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6A		34	40	m ohm	
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V	-30			A	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -10A		11.5		S	
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>							
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz		1130		pF	
Output Capacitance	C <sub>OSS</sub>			270		pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>			170		pF	
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>							
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = -15V I <sub>D</sub> = -1 A V <sub>GS</sub> = -10V R <sub>GEN</sub> = 6 ohm		19		ns	
Rise Time	t <sub>r</sub>			31		ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>			100		ns	
Fall Time	t <sub>f</sub>			28		ns	
Total Gate Charge (10V)	Q <sub>g</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -12A V <sub>GS</sub> = -10V		22		nC	
Total Gate Charge (4.5V)				10.6		nC	
Gate-Source Charge			Q <sub>gs</sub>		2.7		nC
Gate-Drain Charge			Q <sub>gd</sub>		6.4		nC

# STU/D303S

## ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS <sup>a</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_s = -10A$		-0.88	-1.3	V

### Notes

- a. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

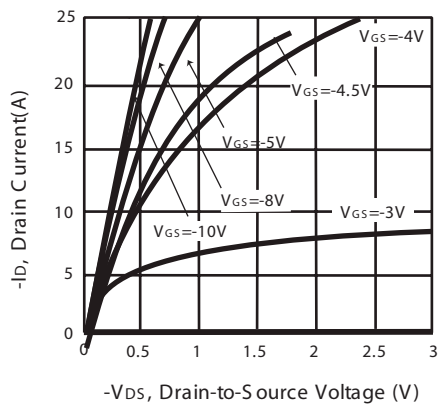


Figure 1. Output Characteristics

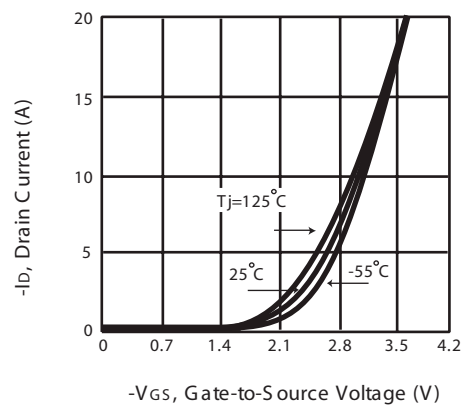


Figure 2. Transfer Characteristics

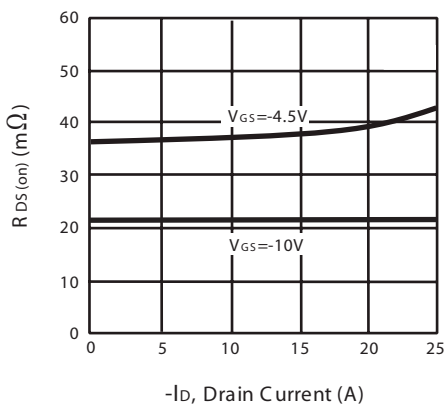


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

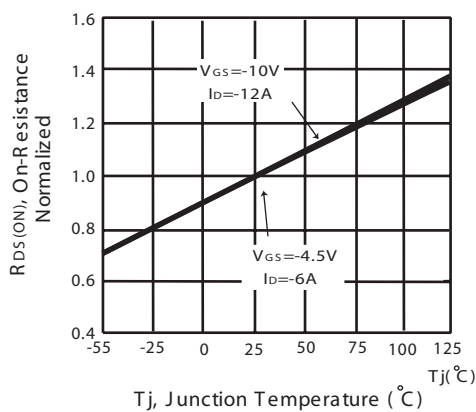


Figure 4. On-Resistance Variation with Drain Current and Temperature

# STU/D303S

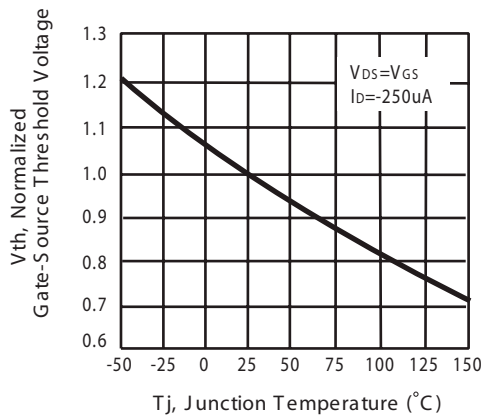


Figure 5. Gate Threshold Variation with Temperature

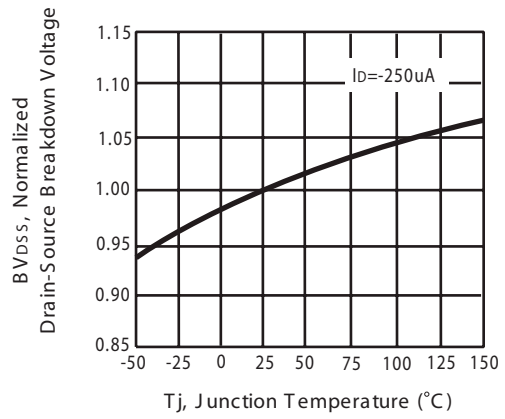


Figure 6. Breakdown Voltage Variation with Temperature

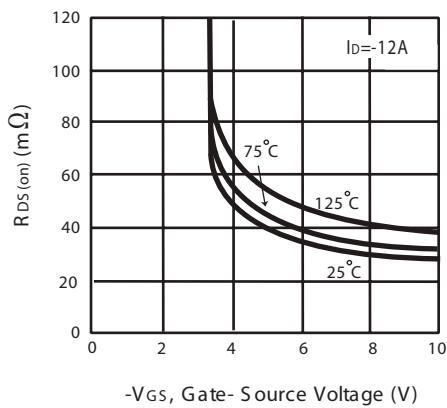


Figure 7. On-Resistance vs. Gate-Source Voltage

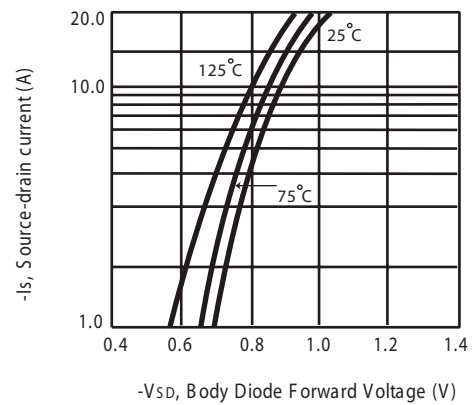


Figure 8. Body Diode Forward Voltage Variation with Source Current

# STU/D303S

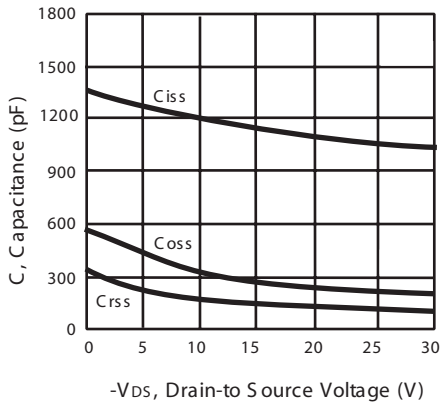


Figure 9. Capacitance

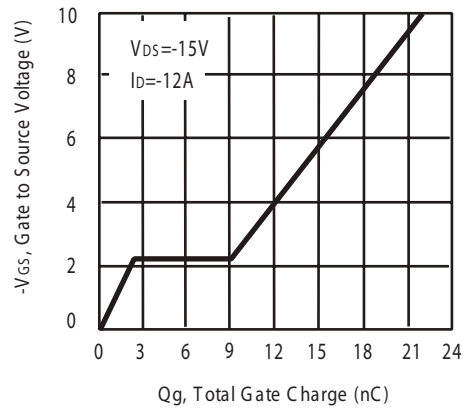


Figure 10. Gate Charge

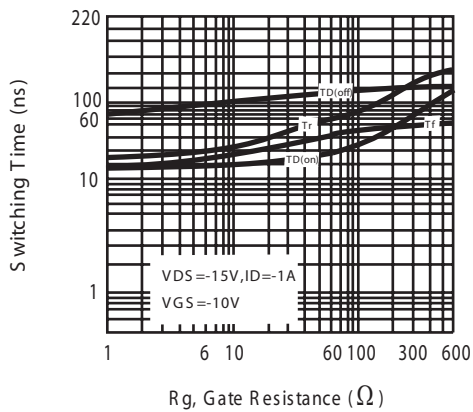


Figure 11. switching characteristics

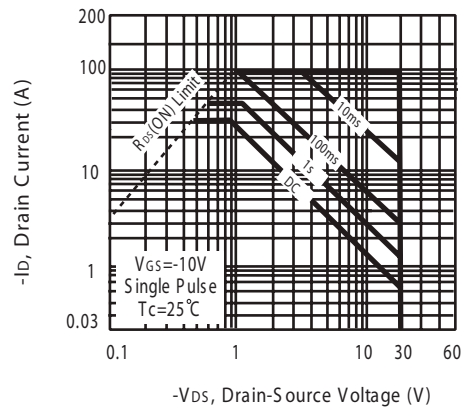


Figure 12. Maximum Safe Operating Area

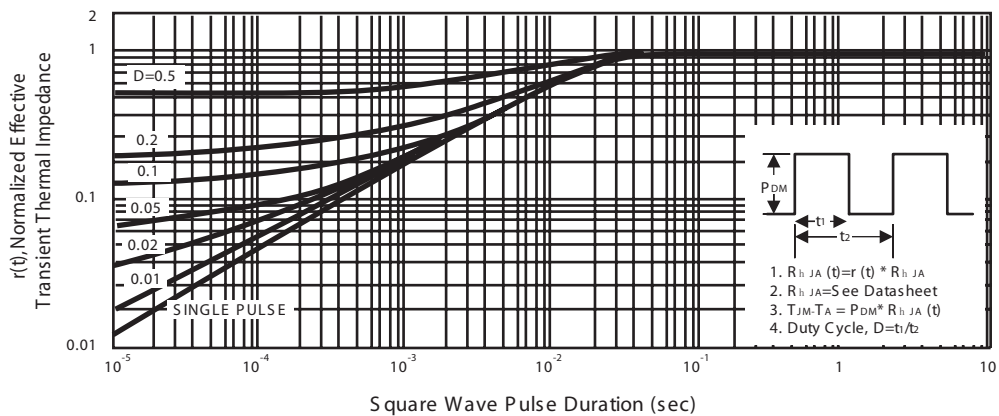
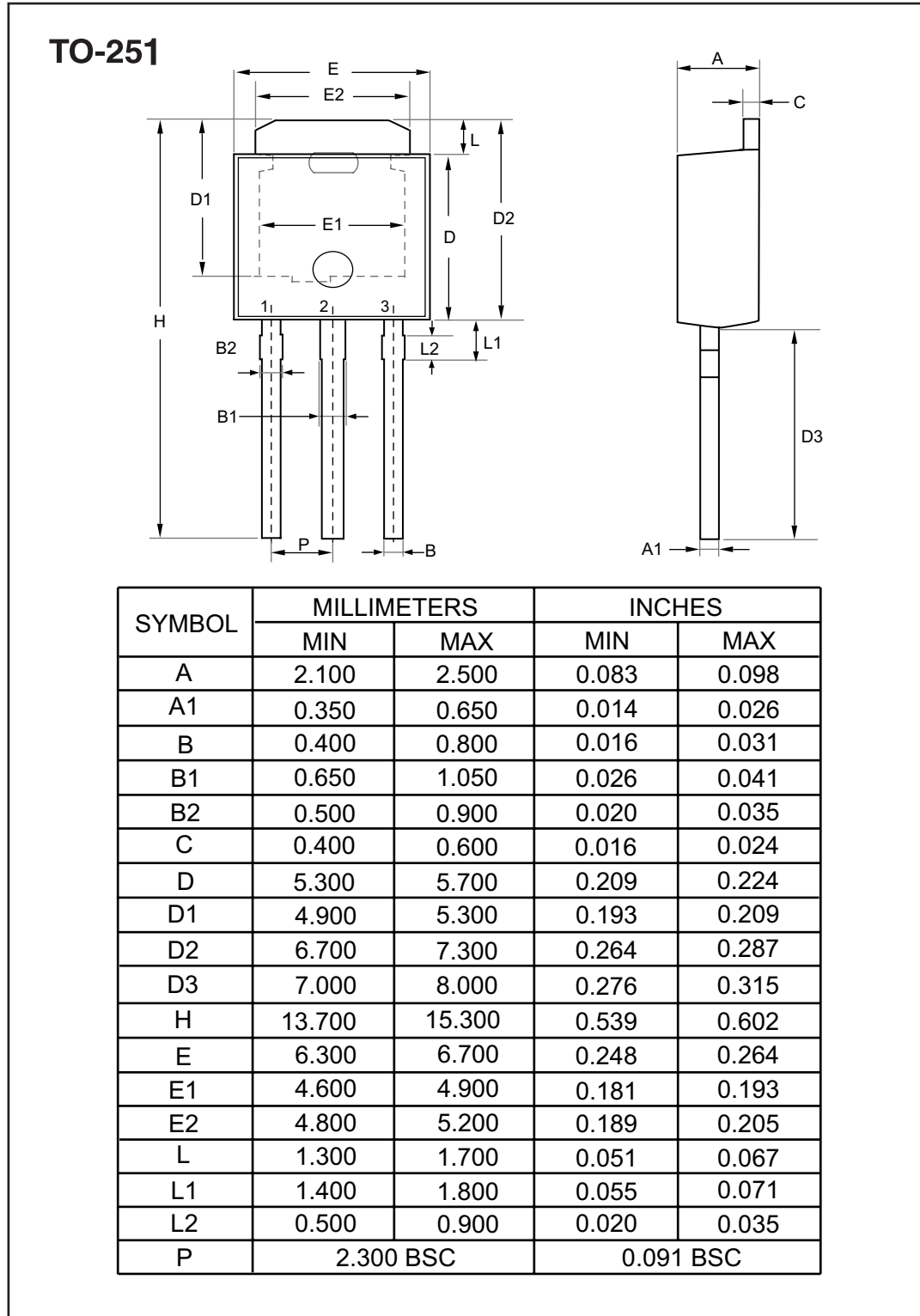


Figure 13. Normalized Thermal Transient Impedance Curve

# STU/D303S

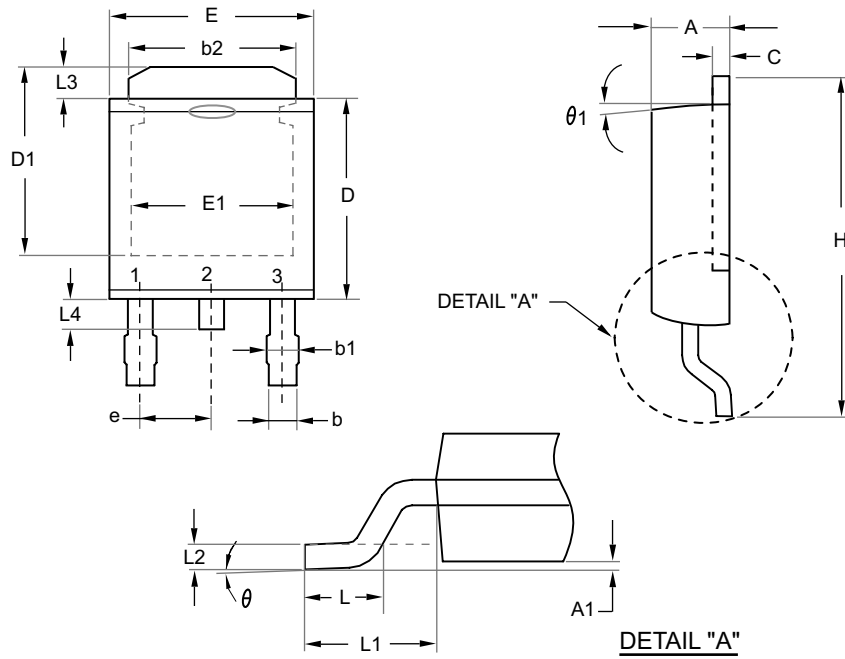
## PACKAGE OUTLINE DIMENSIONS



# STU/D303S

## PACKAGE OUTLINE DIMENSIONS

TO-252

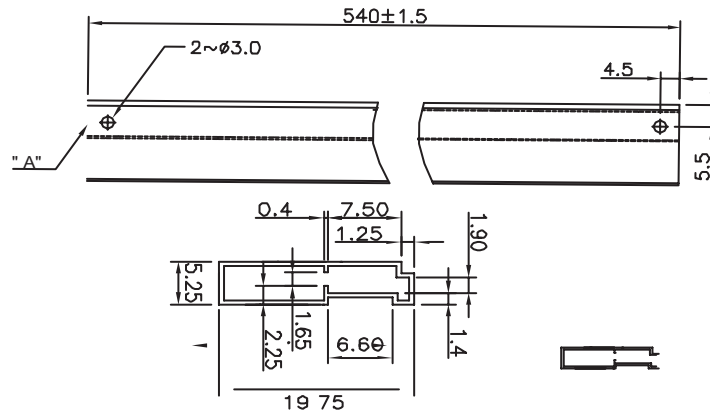


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
$\theta$	0°	10°	0°	10°
$\theta_1$	7° REF.		7° REF.	

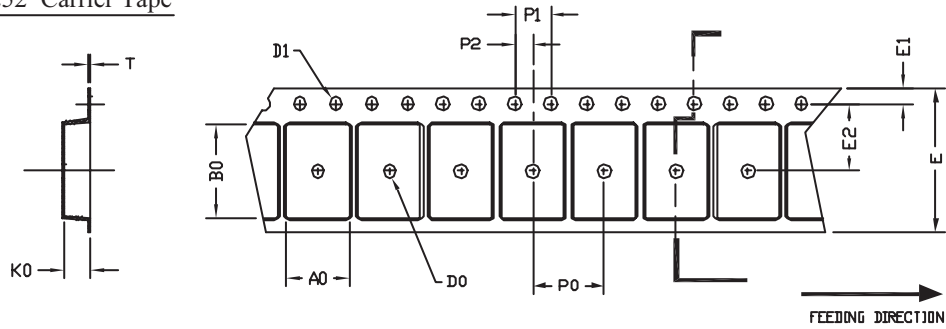
# STU/D303S

## TO251 Tube/TO-252 Tape and Reel Data

### TO-251 Tube



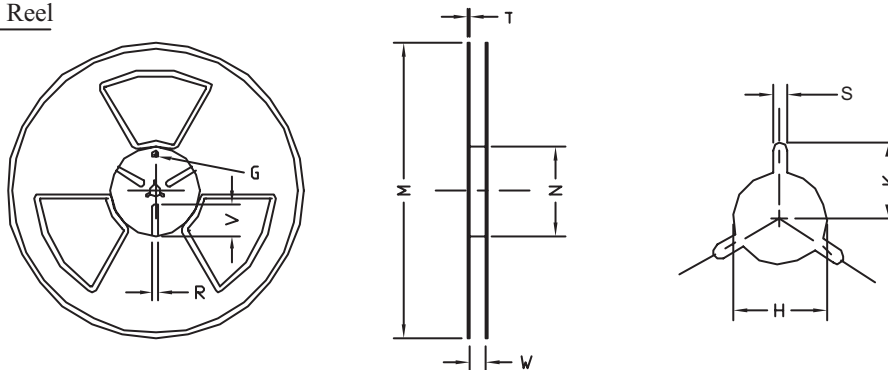
### TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 0.3±	1.75 0.1±	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

### TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---